

Vishay Semiconductors

ROHS

HALOGEN

FREE

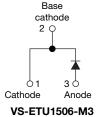
Ultrafast Rectifier, 15 A FRED Pt®



2L TO-220AC



2L TO-220 FULL-PAK





VS-ETU1506FP-M3

PRODUCT SUMMARY				
Package	2L TO-220AC, 2L TO-220FP			
I _{F(AV)}	15 A			
V_{R}	600 V			
V _F at I _F	1.1 V			
t _{rr} (typ.)	24 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Low forward voltage drop
- · Ultrafast soft recovery time
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION

State of the art, ultralow V_F , soft-switching ultrafast rectifiers optimized for Discontinuous (Critical) Mode (DCM) Power Factor Correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimized the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

APPLICATIONS

AC/DC SMPS 70 W to 400 W

e.g. laptop and printer AC adaptors, desktop PC, TV and monitor, games units and DVD AC/DC power supplies.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		600	V		
A	I _{F(AV)}	T _C = 151 °C	15	А		
Average rectified forward current in DC FULL-PAK		T _C = 103 °C	15			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	160			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-		
Forward voltage V	\/_	I _F = 15 A	-	1.35	1.9	V	
	v _F	I _F = 15 A, T _J = 150 °C	-	1.1	1.3		
Devenue le alcono everent	_	$V_R = V_R$ rated	-	0.01	15		
Reverse leakage current I_R $T_J = 150$		T _J = 150 °C, V _R = V _R rated	-	20	200	μA	
Junction capacitance	C _T	V _R = 600 V	-	12	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 100$	$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		24	28	
Reverse recovery time		$I_F = 15 \text{ A}, dI_F/dt = 10$	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		36	47	
neverse recovery time	t _{rr}	T _J = 25 °C		-	40	-	ns
		T _J = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	87	-	
Peak recovery current	1	T _J = 25 °C		-	5	-	А
reak recovery current	I _{RRM}	T _J = 125 °C		-	9	-	
Devene vecesient eberge		T _J = 25 °C		-	107	-	nC
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	430	-	nc
Reverse recovery time	t _{rr}	T _J = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 800 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	53	-	ns
Peak recovery current	I _{RRM}			-	25	-	Α
Reverse recovery charge	Q _{rr}			-	730	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance,	D		ı	1.2	1.4	
junction to case FULL-PAK	R_{thJC}		-	3.7	4.3	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
\\/-:- -t			-	2	-	g
Weight			-	0.07	-	oz.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Marking daying		Case style 2L TO-220AC	ETU1506			
Marking device		Case style 2L TO-220 FULL-PAK		ETU1	506FP	



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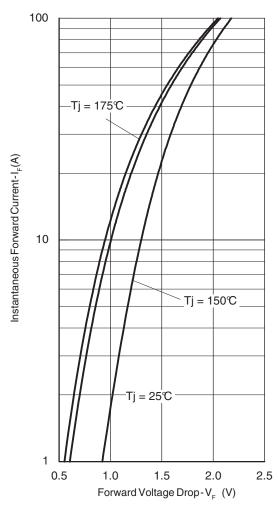


Fig. 1 - Typical Forward Voltage Drop Characteristics

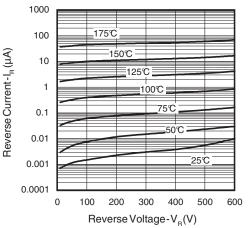


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

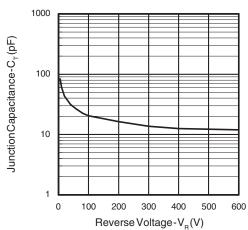


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

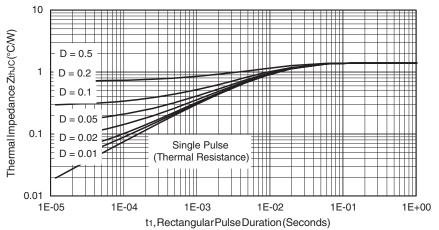


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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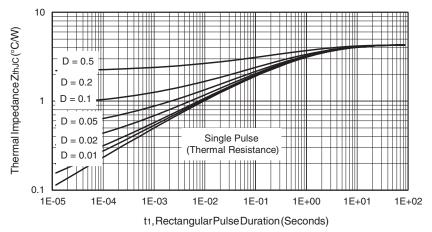


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

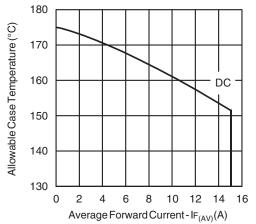


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

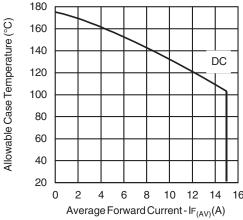


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

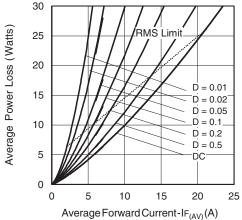


Fig. 8 - Forward Power Loss Characteristics

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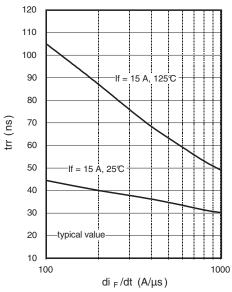


Fig. 9 - Typical Reverse Recovery vs. dl_F/dt

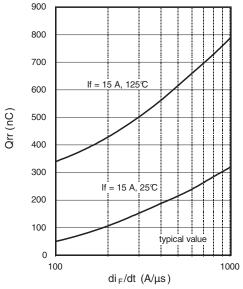


Fig. 10 - Typical Stored Charge vs. dl_F/dt

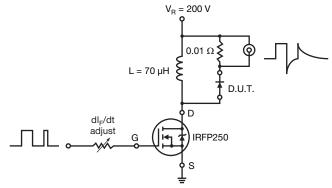
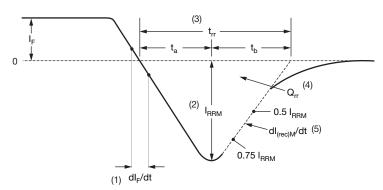


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

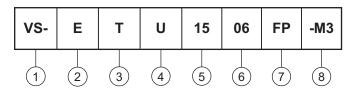
Fig. 12 - Reverse Recovery Waveform and Definitions

VS-ETU1506-M3,VS-ETU1506FP-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Circuit configuration:

E = single diode

3 - T = TO-220

U = hyperfast recovery time

Current code: 15 = 15 A

Voltage code: 06 = 600 V

7 - • None = TO-220

• FP = FULL-PAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-ETU1506-M3	50	1000	Antistatic plastic tube			
VS-ETU1506FP-M3	50	1000	Antistatic plastic tube			

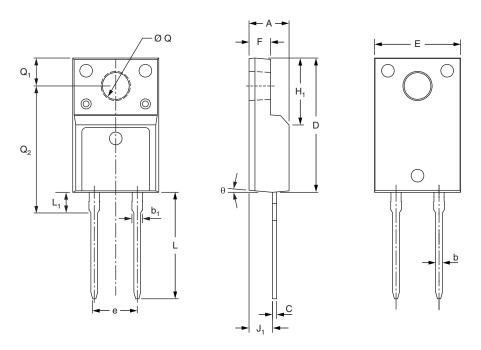
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95259				
Dimensions	2L TO-220 FULL-PAK	www.vishay.com/doc?95260			
Part marking information	2L TO-220AC	www.vishay.com/doc?95391			
Fait marking information	2L TO-220 FULL-PAK	www.vishay.com/doc?95392			



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True 2 Pin TO-220 FULL-PAK

DIMENSIONS in millimeters and inches



CYMPOL	MILLIM	METERS	INCH	IES
SYMBOL	MIN.	MAX.	MIN.	MAX.
A	4.53	4.93	0.178	0.194
b	0.71	0.91	0.028	0.036
b ₁	1.15	1.39	0.045	0.055
С	0.36	0.53	0.014	0.021
D	15.67	16.07	0.617	0.633
E	9.96	10.36	0.392	0.408
е	5.08 t	ypical	0.200 ty	ypical
F	2.34	2.74	0.092	0.107
H ₁	6.50	6.90	0.256	0.272
J ₁	2.56	2.96	0.101	0.117
L	12.78	13.18	0.503	0.519
L ₁	2.23	2.63	0.088	0.104
ØQ	2.98	3.38	0.117	0.133
Q ₁	3.10	3.50	0.122	0.138
Q_2	14.80	15.20	0.583	0.598
θ	0°	5°	0°	5°



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